

# TGBR10V150

Advance

DIODE

# TRENCH MOS SCHOTTKY BARRIER RECTIFIER

### DESCRIPTION

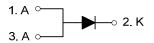
The UTC **TGBR10V150** is a trench mos schottky barrier rectifier, it uses UTC's advanced technology to provide customers with low forward voltage drop and high current capability, etc.

The UTC **TGBR10V150** suitable for free wheeling, high frequency inverters, polarity protection, and low voltage.

## FEATURES

- \* Very low forward voltage drop
- \* High current capability
- \* High surge capability
- \* High efficiency

#### SYMBOL

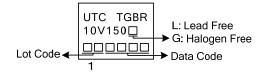


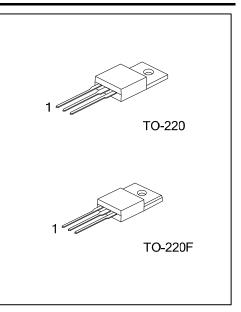
#### ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Booking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
TGBR10V150L-TA3-T	TGBR10V150G-TA3-T	TO-220	А	К	А	Tube	
TGBR10V150L-TF3-T	TGBR10V150G-TF3-T	TO-220F	А	К	А	Tube	
Note: Pin Assignment: A: Anode K: Cathode							

TGBR10V150L-TA3-T	(1) T: Tube
(2)Package Type	(2) TA3: TO-220, TF3: TO-220F
(3)Green Package	(3) L: Lead Free, G: Halogen Free and Lead Free

#### MARKING





#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by	20 /0.			
PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage (Note 1)		V <sub>RM</sub>	150	V
Working Peak Reverse Voltage		V <sub>RWM</sub>	150	V
Peak Repetitive Reverse Voltage		V <sub>RRM</sub>	150	V
RMS Reverse Voltage		V <sub>R(RMS)</sub>	35	V
Average Rectified Output Current	T <sub>C</sub> =125°C	lo	10	А
Ion-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I <sub>FSM</sub>	150	А
Operating Junction Temperature		TJ	-65~+150	°C
Storage Temperature		T <sub>STG</sub>	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL CHARACTERISTICS (PER LEG)

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ <sub>JA</sub>	62.5	°C/W
Junction to Case	TO-220	0	2	°C/W
	TO-220F	θ <sub>JC</sub>	3.31	C/VV

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub> =25°C unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub> I <sub>R</sub> =0.50mA		150			V
Forward Voltage Drop	VEM	I <sub>F</sub> =10A, T <sub>C</sub> =25°C			0.85	V
		I <sub>F</sub> =10A, T <sub>C</sub> =125°C			0.75	V
Peak Reverse Current at Rated DC	DM	V <sub>R</sub> =150V, T <sub>C</sub> =25°C			200	μA
Blocking Voltage (Note 1)		V <sub>R</sub> =150V, T <sub>C</sub> =125°C			50	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

2. Thermal resistance junction to case mounted on heatsink.

3. Mounted on an FR4 PCB, single-sided copper, with 150cm<sup>2</sup> copper pad area.



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